Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	10/775908	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:04
L2	1850562	(dioxide oxide SiO "SiO.sub.2" "SiO.sub.x")	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:05
L3	511736	(nitride SiN "SiN.sub.2" "SiN.sub.3" "SiN.sub.4" "SiN.sub.x" ono oxynitride nitride)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:07
L4	297016	((high hi) adj (dielectric k) hfo zro tio tao lao alo (hafnium zirconium tantalum titanium lanthan\$3 aluminum) adj (oxide pentoxide) "hf.sub.o" "zr.sub.o" "ti.sub.o" "ta.sub.o" "la.sub.o" "al.sub.o")	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:07
L5	6585	(hfo hafnium adj (oxide pentoxide) "hf.sub.o")	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:09
L6	6586	(hfo hafnium adj (oxide pentoxide) "hf.sub.o" "hf.sub.o. sub.2" "hf.sub.o.sub.x")	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:10
L7	30287	2 with 3 with 4	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:10
L8	5158478	transistor gate source drain channel	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:10

L9	5184564	transistor gate source drain channel tft fet mosfet cfet cmosfet ?fet ?tft	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:12
L10	5184631	transistor gate source drain channel tft fet mosfet cfet cmosfet ?fet ?tft \$ntft \$nfet	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:12
L11	4838	7 same 10	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:13
L12	31958602	(@ad @pd) < "20040209"	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:13
L13	3523	11 and 12	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:15
L14	4728010	memory storage charge electron	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:15
L15	14374	3 near6 14	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:17
L16	374	13 and 15	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:31

L18	3403131	(intergate interpoly interelectrode inter adj (poly gate electrode) block\$4 IGI IGD)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:32
L19	188660	tunnel\$4	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:34
L20	61	(18 19) near8 5	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:35
L21	172	(18 19) with 5	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:36
L22	8	16 and 21	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:47
L23	2289	(257/324,411,E29.309).CCLS.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/01 10:47
L24	14	23 and 21	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 12:15
L25	42	15 and 21	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 12:16

L26	16	25 and 12	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 12:17
L27	26	25 not 26	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 12:17
L28	4	("6903407").URPN.	USPAT	OR	ON	2006/09/01 12:19
L29	2	("6639271" "6735123").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/01 12:19